



## 100V 3.1mΩ N-Ch Power MOSFET

### Features

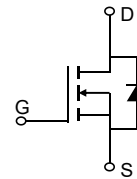
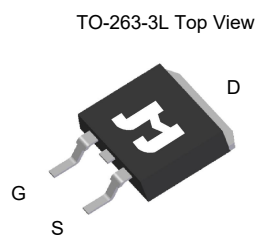
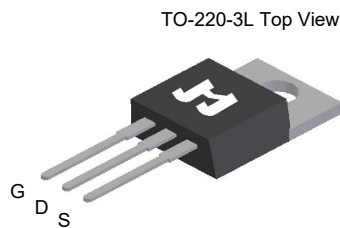
- Ultra-low  $R_{DS(ON)}$
- Low Gate Charge
- 100% UIS Tested, 100%  $R_g$  Tested
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant

### Product Summary

Parameter	Value	Unit
$V_{DS}$	100	V
$V_{GS(th)}$ Typ	3.2	V
$I_D$ (@ $V_{GS} = 10V$ ) <sup>(1)</sup>	175	A
$R_{DS(ON)}$ Typ (@ $V_{GS} = 10V$ )	3.1	mΩ

### Applications

- Motor Driving in Power Tool, E-vehicle, Robotics
- Current Switching in DC/DC & AC/DC (SR) Sub-systems
- Power Management in Telecom., Industrial Automation, CE

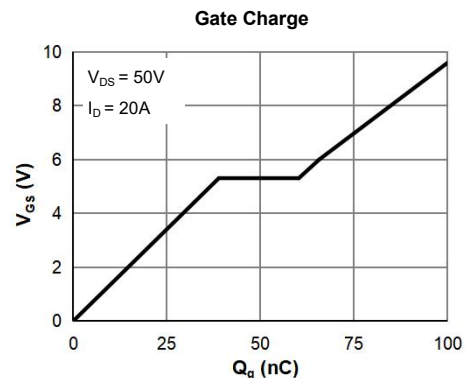
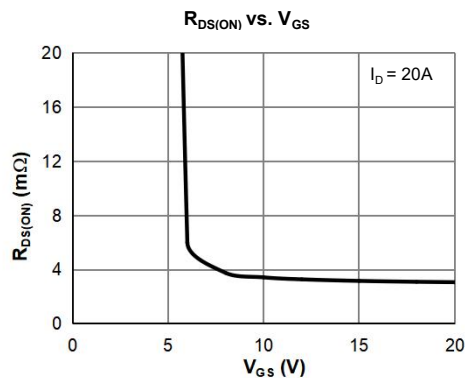


### Ordering Information

Device	Package	# of Pins	Marking	MSL	$T_J$ (°C)	Media	Quantity (pcs)
JMSH1002YC-U	TO-220-3L	3	SH1002Y	NA	-55 to 150	Tube	50
JMSH1002YE-13	TO-263-3L	3	SH1002Y	3	-55 to 150	13-inch Reel	800

**Absolute Maximum Ratings** (@  $T_A = 25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DS}$	100	V
Gate-to-Source Voltage	$V_{GS}$	±20	V
Continuous Drain Current <sup>(1)</sup>	$I_D$	$T_C = 25^\circ\text{C}$	175
		$T_C = 100^\circ\text{C}$	110
Pulsed Drain Current <sup>(2)</sup>	$I_{DM}$	700	A
Avalanche Energy <sup>(3)</sup>	$E_{AS}$	600	mJ
Power Dissipation <sup>(4)</sup>	$P_D$	$T_C = 25^\circ\text{C}$	250
		$T_C = 100^\circ\text{C}$	100
Junction & Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	°C





**Electrical Characteristics** (@  $T_J = 25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>STATIC PARAMETERS</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	100			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 80\text{V}, V_{GS} = 0\text{V}$ $T_J = 55^\circ\text{C}$			1.0 5.0	$\mu\text{A}$
Gate-Body Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2.0	3.2	4.0	V
Static Drain-Source ON-Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}, I_D = 20\text{A}$	TO-263-3L	3.1	3.7	m $\Omega$
			TO-220-3L	3.3	4.0	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS} = 5\text{V}, I_D = 20\text{A}$		47.8		S
Diode Forward Voltage	$V_{SD}$	$I_S = 1\text{A}, V_{GS} = 0\text{V}$		0.70	1.0	V
Diode Continuous Current	$I_S$	$T_C = 25^\circ\text{C}$			175	A

**DYNAMIC PARAMETERS** <sup>(5)</sup>

Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 50\text{V}, f = 1\text{MHz}$		7168		pF
Output Capacitance	$C_{oss}$			1067		pF
Reverse Transfer Capacitance	$C_{rss}$			36		pF
Gate Resistance	$R_g$	$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}, f = 1\text{MHz}$		2.7		$\Omega$

**SWITCHING PARAMETERS** <sup>(5)</sup>

Total Gate Charge (@ $V_{GS} = 10\text{V}$ )	$Q_g$	$V_{GS} = 0 \text{ to } 10\text{V}$ $V_{DS} = 50\text{V}, I_D = 20\text{A}$		104		nC
Total Gate Charge (@ $V_{GS} = 6\text{V}$ )	$Q_g$			66		nC
Gate Source Charge	$Q_{gs}$			39		nC
Gate Drain Charge	$Q_{gd}$			21		nC
Turn-On DelayTime	$t_{D(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 50\text{V}$ $R_L = 2.5\Omega, R_{GEN} = 3\Omega$		22		ns
Turn-On Rise Time	$t_r$			32		ns
Turn-Off DelayTime	$t_{D(off)}$			62		ns
Turn-Off Fall Time	$t_f$			36		ns
Body Diode Reverse Recovery Time	$t_{rr}$		$I_F = 15\text{A}, di_F/dt = 100\text{A}/\mu\text{S}$		95	
Body Diode Reverse Recovery Charge	$Q_{rr}$	$I_F = 15\text{A}, di_F/dt = 100\text{A}/\mu\text{S}$		299		nC

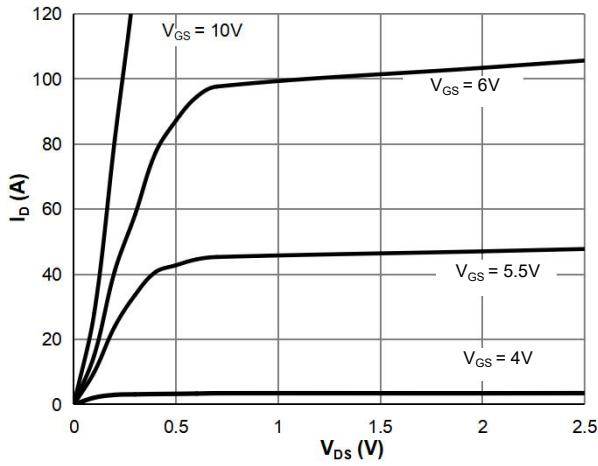
**Thermal Performance**

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	59	68	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.42	0.50	$^\circ\text{C}/\text{W}$

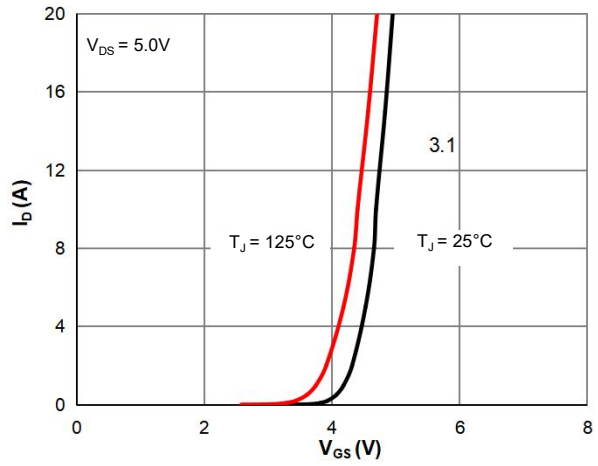
**Notes:**

1. Computed continuous current assumes the condition of  $T_{J\_Max}$  while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under  $T_{J\_Max} = 150^\circ\text{C}$ .
3.  $E_{AS}$  of 600mJ is based on starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.5\text{mH}$ ,  $I_{AS} = 49.7\text{A}$ ,  $V_{GS} = 10\text{V}$ ,  $V_{DD} = 50\text{V}$ ; 100% test at  $L = 0.1\text{mH}$ ,  $I_{AS} = 69.6\text{A}$ .
4. The power dissipation  $P_D$  is based on  $T_{J\_Max} = 150^\circ\text{C}$ .
5. This value is guaranteed by design hence it is not included in the production test.

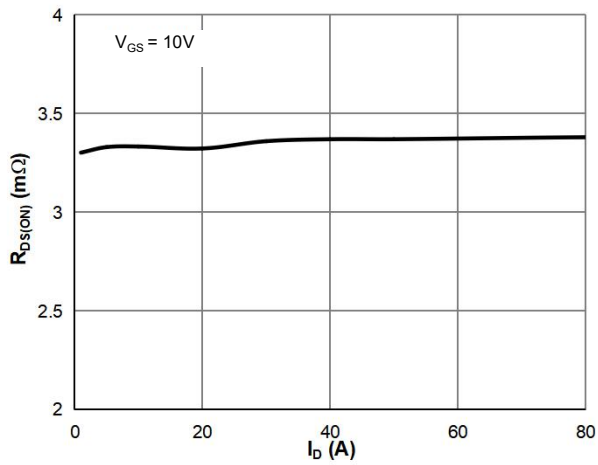
**Typical Electrical & Thermal Characteristics**



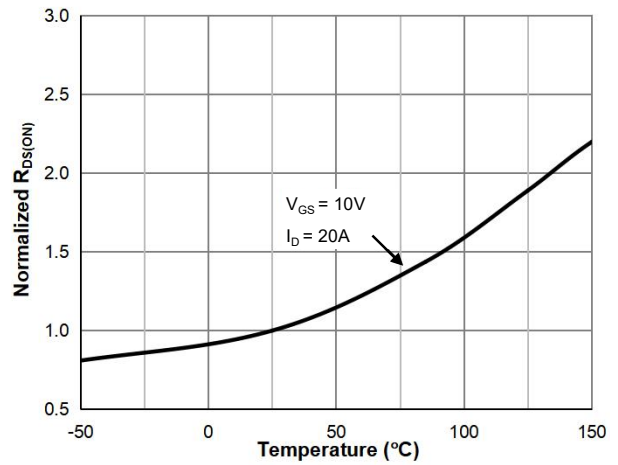
**Figure 1: Saturation Characteristics**



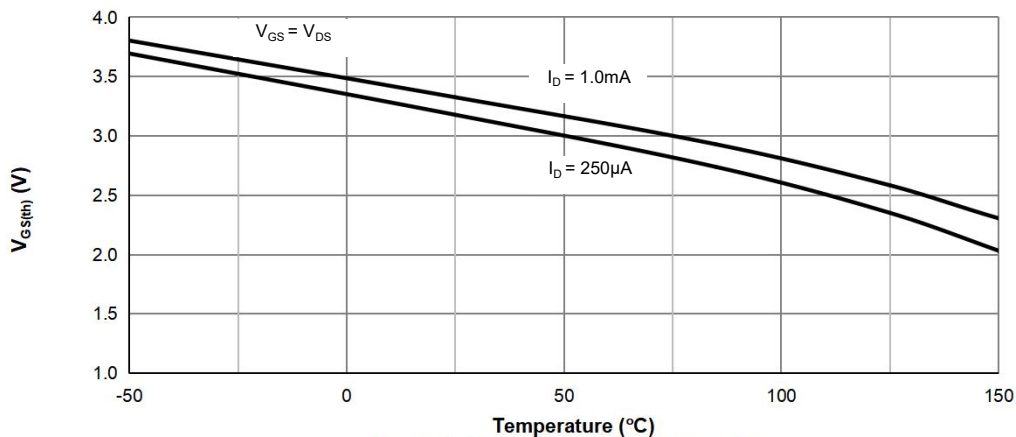
**Figure 2: Transfer Characteristics**



**Figure 3:  $R_{DS(ON)}$  vs. Drain Current**



**Figure 4:  $R_{DS(ON)}$  vs. Junction Temperature**



**Figure 5:  $V_{GS(th)}$  vs. Junction Temperature**

Typical Electrical & Thermal Characteristics

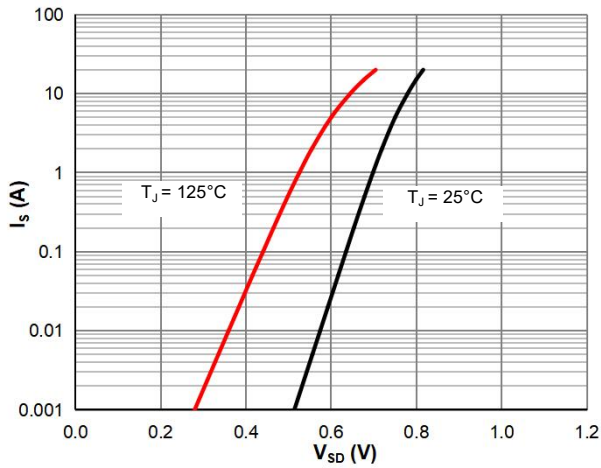


Figure 7: Body-Diode Characteristics

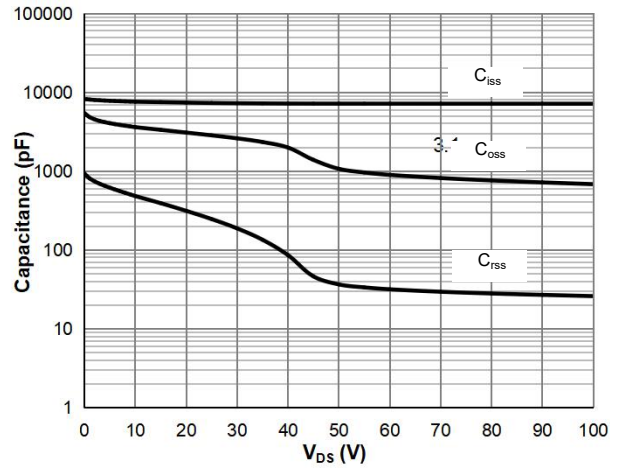


Figure 8: Capacitance Characteristics

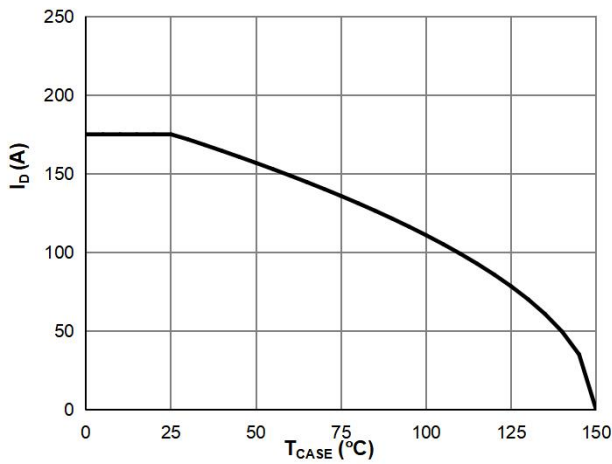


Figure 9: Current De-rating

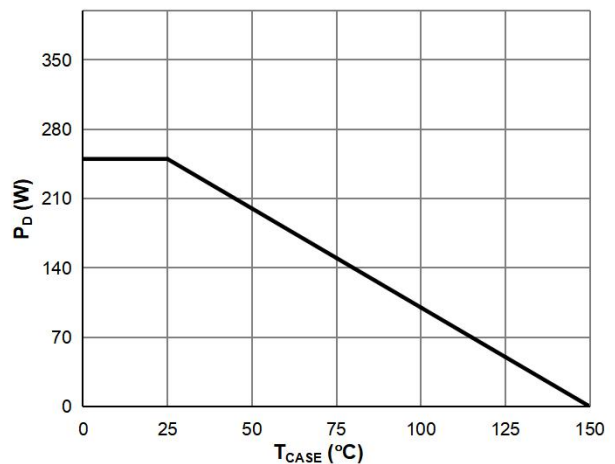


Figure 10: Power De-rating

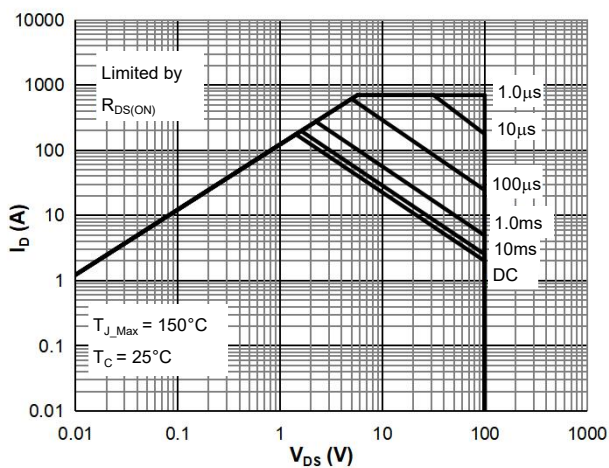


Figure 11: Maximum Safe Operating Area

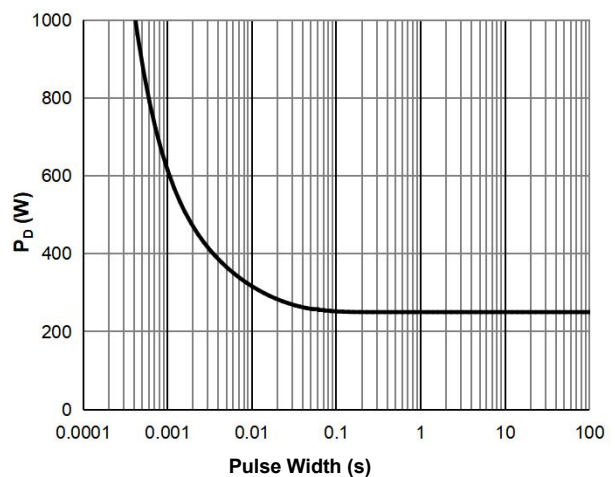


Figure 12: Single Pulse Power Rating, Junction-to-Case

Typical Electrical & Thermal Characteristics

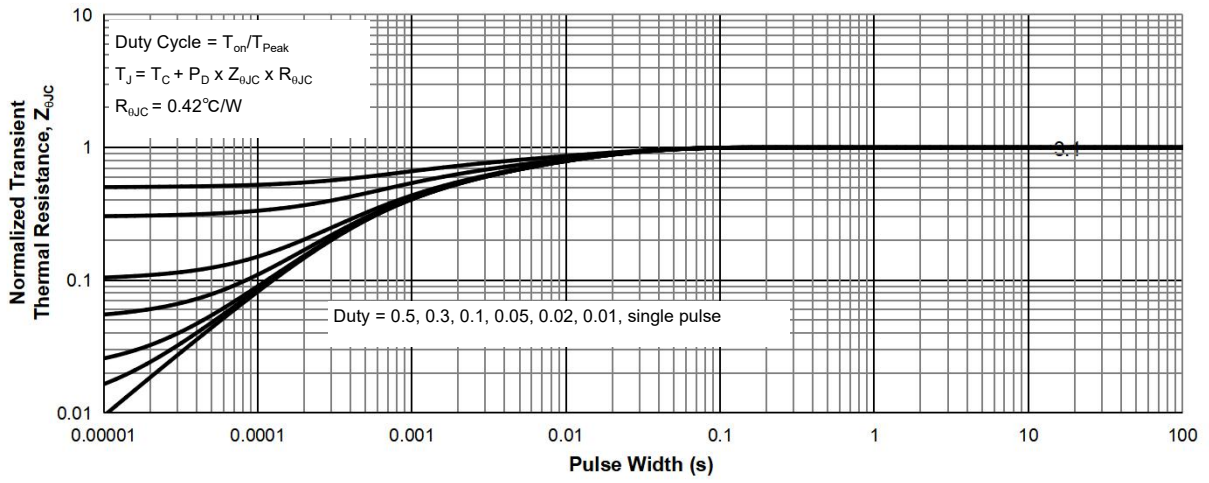
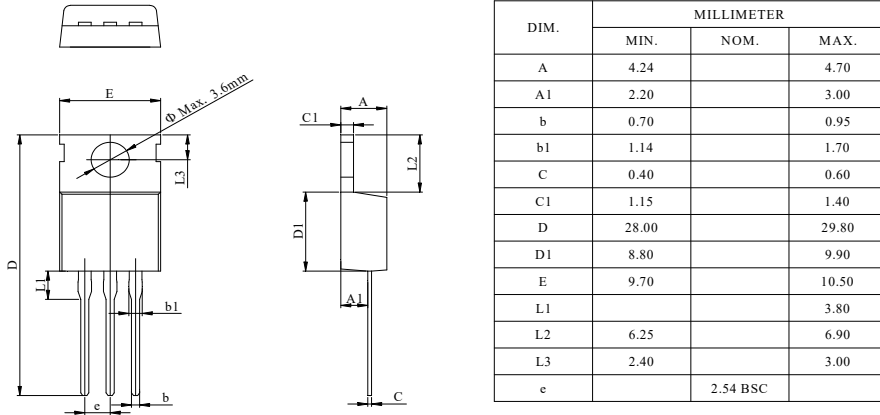


Figure 13: Normalized Maximum Transient Thermal Impedance

**TO-220-3L Package Information**

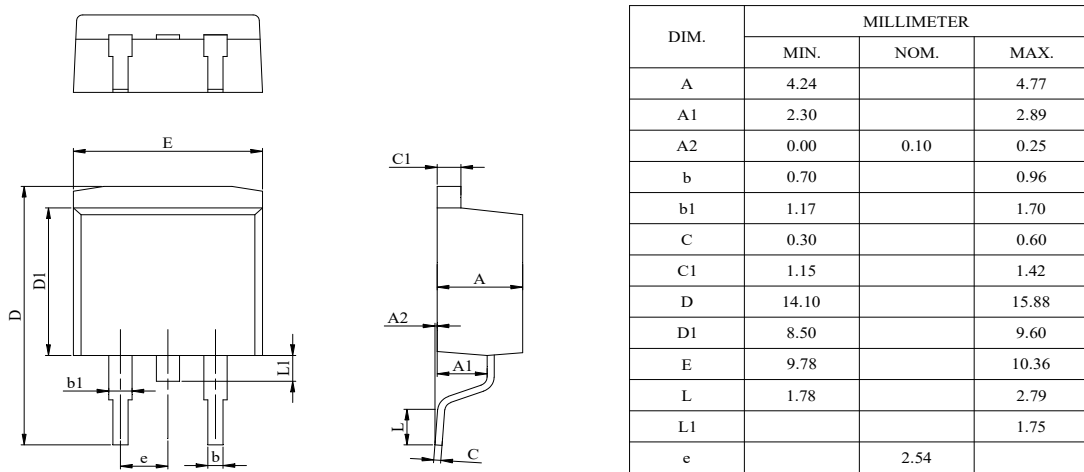
**Package Outline**



3.1

**TO-263-3L Package Information**

**Package Outline**



**Recommend Soldering Footprint**

